

Non-Contact Methods of Measuring Stresses in High Temperature Materials

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*Everyone talks about the weather..
but nobody does anything about it*

*Mark Twain
(Samuel Clemens)*

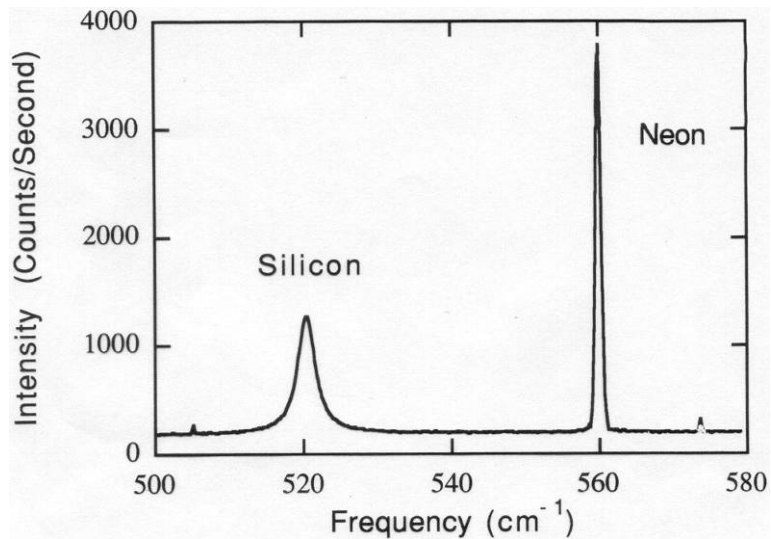
*Everyone talks about **stresses**.....
but nobody does anything about them*

Outline

- Introduction to Cr³⁺ based luminescence and piezospectroscopy (luminescence and Raman).
- Phase transformations during the growth of alumina by thermal oxidation
- Latest developments on piezospectroscopy
- Modes of strain energy relief in oxide films and coatings
- Wrinkling, wrinkling kinetics leading to oxide film failure
- Buckling and buckle growth
- Conditions for spalling by the growth of buckles
- Large scale buckling
- Rumpling
- Monitoring damage evolution in TBCs by piezospectroscopy
- Summary

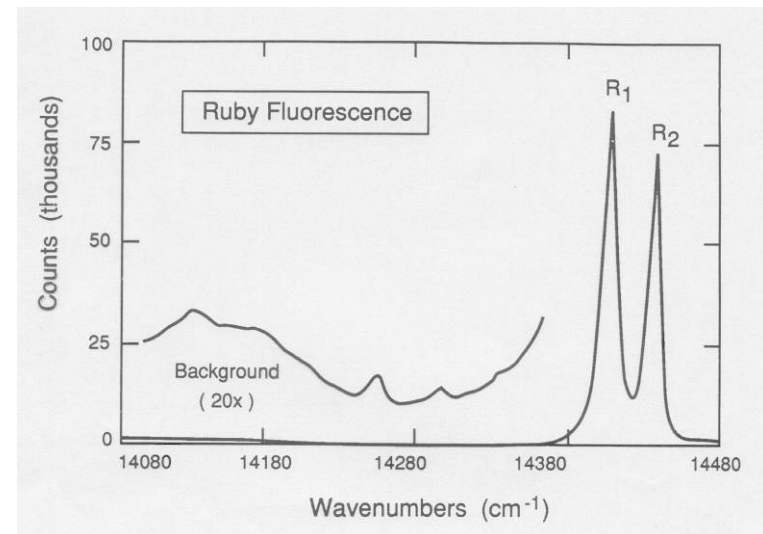
Principal Types of Piezospectroscopy

Vibrational piezospectroscopy –
Raman piezospectroscopy



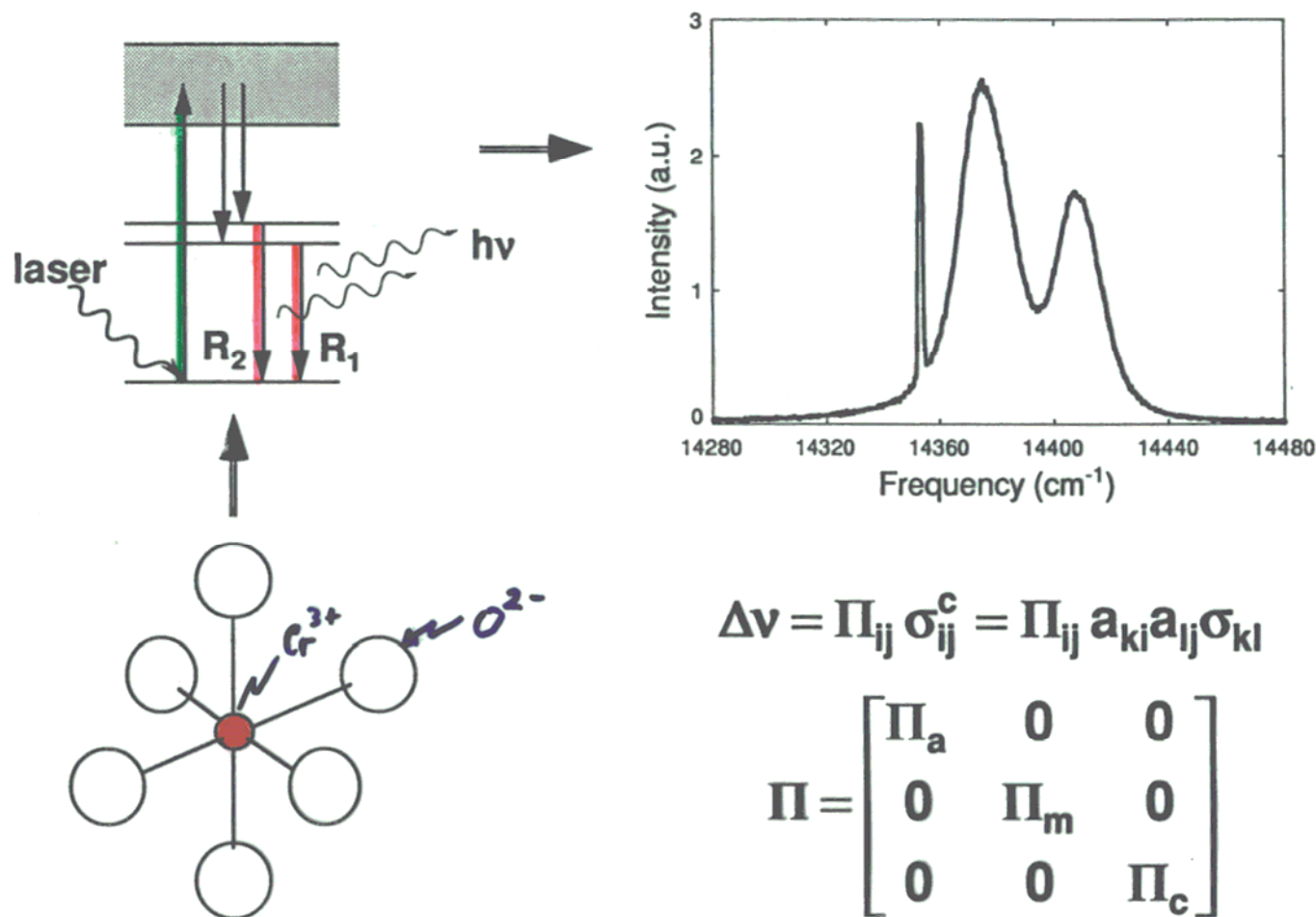
Single crystal silicon

Luminescence piezospectroscopy



Sapphire containing Cr dopant

Physical Basis of Luminescence Piezospectroscopy: Synopsis



Octahedral coordination of Cr³⁺

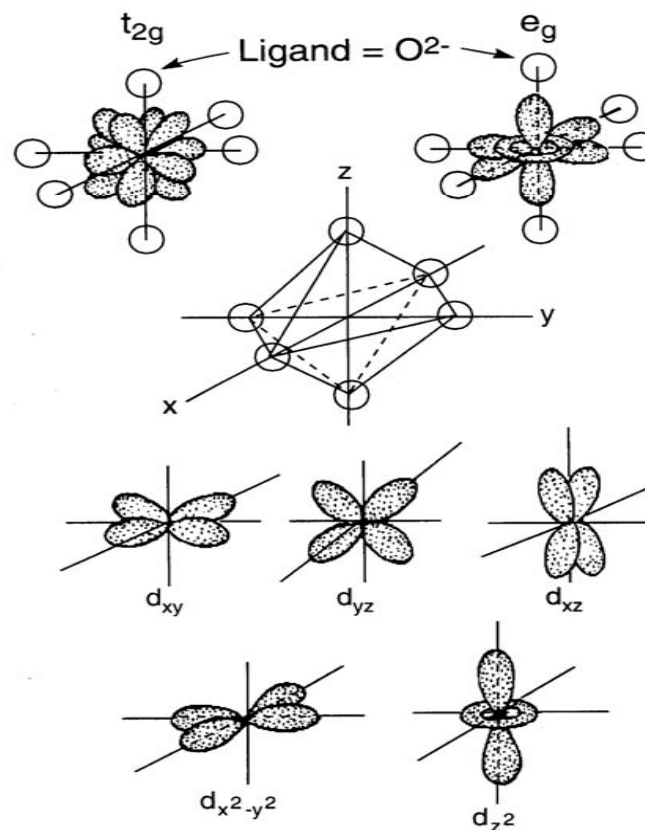
$$\Delta\nu = \Pi_{ij} \sigma_{ij}^c = \Pi_{ij} a_{ki} a_{lj} \sigma_{kl}$$

$$\Pi = \begin{bmatrix} \Pi_a & 0 & 0 \\ 0 & \Pi_m & 0 \\ 0 & 0 & \Pi_c \end{bmatrix}$$

Piezospectroscopy Relation

Electronic Transitions of d^3 Electrons

Electron Config-uration	Cubic Field Terms	Including Trigonal Distortion	Including Spin-Orbit Interaction	Eigen-state	Energy (cm ⁻¹)
$t_2^2 e$	4T_1		$\sim \zeta$	4A_2	25200
				4E	24400
t_2^3	2T_2		$\sim \zeta k$	$\bar{E}_b$	21360
				$\bar{E}_a$	21070
				$\frac{2\bar{A}}{2A}$	21000
$t_2^2 e$	4T_2		$\sim \zeta$	4A_1	18450
				4E	18000
t_2^3	2T_1		$\sim \zeta k$	$\bar{E}_a$	15190
				$\frac{2\bar{A}}{2A}$	15170
				$\bar{E}_b$	14960
t_2^3	2E		$\sim \zeta k$	$\bar{2A}$	14430
				$\bar{E}$	14400
t_2^3	4A_2		$\sim \zeta^2 k$		0

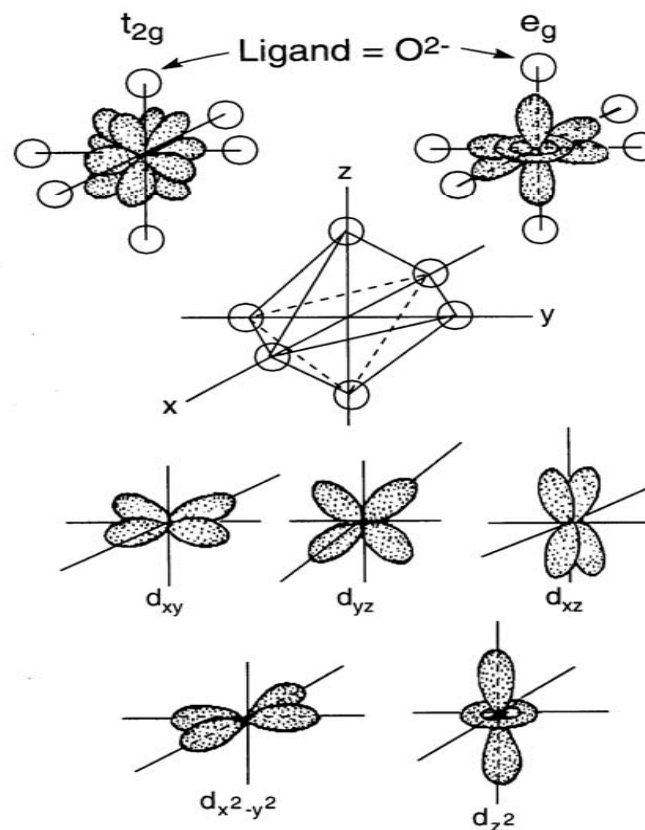


Ambient pressure transitions in the visible

Strain alters ligand length and hence local potential on the electrons.

Electronic Transitions of d^3 Electrons

Electron Config-uration	Cubic Field Terms	Including Trigonal Distortion	Including Spin-Orbit Interaction	Eigen-state	Energy (cm ⁻¹)
$t_2^2 e$	4T_1		$-\zeta$	4A_2	25200
				4E	24400
t_2^3	2T_2		$-\zeta k$	$\bar{E}_b$	21360
				$\bar{E}_a$	21070
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t_2^3	2E		$-\zeta k$	$\bar{2A}$	14430
				$\bar{E}$	14400
t_2^3	4A_2		$-\zeta^2 k$		0



Ambient pressure transitions in the visible

Strain alters ligand length and hence local potential on the electrons.

Cr³⁺ Piezospectroscopy in Sapphire

In crystal coordinates, frequency shift, $\Delta\nu$, is related to stress:

$$\Delta\nu = \Pi_{ij} \sigma_{ij}^c + \Lambda_{ijkl} \sigma_{ij}^c \sigma_{kl}^c$$

where Π_{ij} are the piezo-spectroscopic coefficients.

Point symmetry of Cr³⁺ ion in sapphire imposes condition:

$$\Pi_{11} = \Pi_{22} = \Pi_a \quad : \quad \Pi_{33} = \Pi_c$$

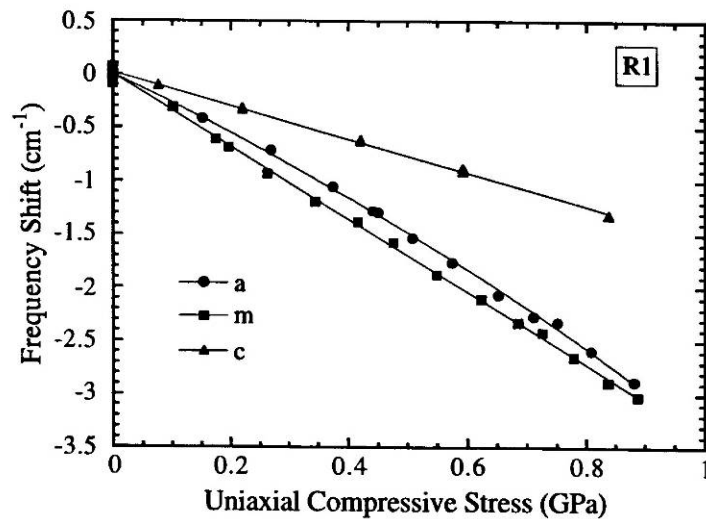
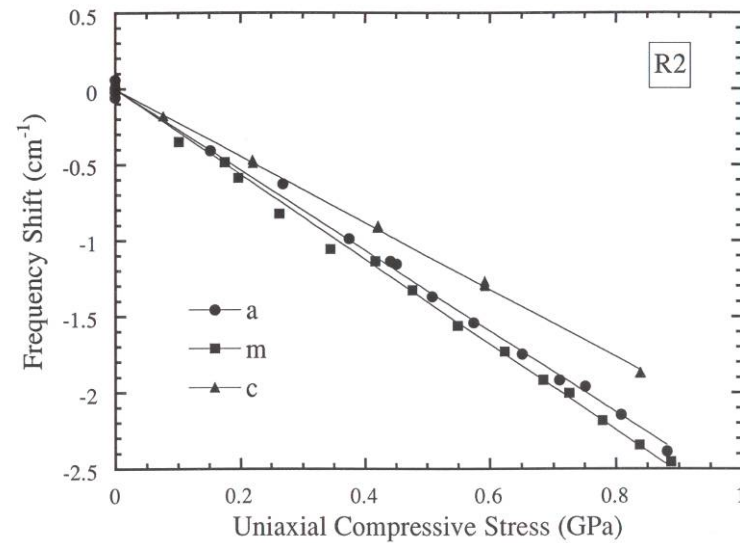
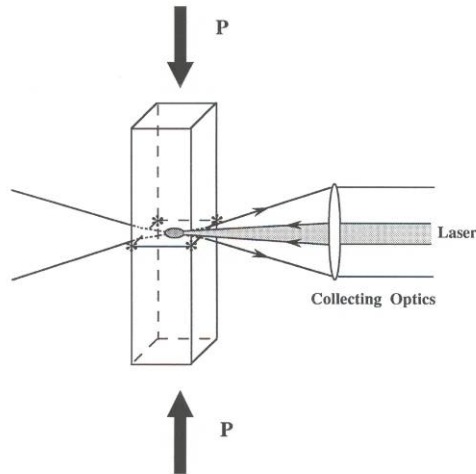
R1 Line:

$$\Pi_{ij} = \begin{pmatrix} 2.56 & 0 & 0 \\ 0 & 3.50 & 0 \\ 0 & 0 & 1.53 \end{pmatrix} \quad cm^{-1}/GPa$$

R2 Line:

$$\Pi_{ij} = \begin{pmatrix} 2.65 & 0 & 0 \\ 0 & 2.80 & 0 \\ 0 & 0 & 2.16 \end{pmatrix} \quad cm^{-1}/GPa$$

Calibration of piezo-spectroscopy coefficients



Piez spectroscopic Coefficients for R lines

	Π_{11}	Π_{22}	Π_{33}	$\Pi_{11} + \Pi_{22} + \Pi_{33}$
	$(\text{cm}^{-1}/\text{GPa})$			
R1	2.56 *	3.50	1.53	7.59
R2	2.65	2.80	2.16	7.61

* Parabolic fitting $\Lambda_{1111} = -0.8 \text{ cm}^{-1}/\text{GPa}^2$

Analysis for General Orientation

- In Crystal Structure Coordinates, x'_i $\Delta v = \pi_{ij} \sigma'_{ij}$
- Point Symmetry of Al_2O_3 (D_{3d}) $\pi_{11} = \pi_{22} \neq \pi_{33}$
 $\pi_{ij} = 0 \quad \delta_{ij} \neq 1$
- Deformation Frame Coordinates, x_i
- Transformation matrix a_{ij} , thus $x_i = a_{ij} x'_j$
- Thus, stress in crystal structure coordinates

$$\sigma'_{ij} = a_{ik} a_{jl} \sigma_{kl}$$

- In general case

$$\Delta v = \pi_{11}(\sigma_{11} + \sigma_{22} + \sigma_{33}) + (\pi_{33} - \pi_{11})(a_{31}^2 \sigma_{11} + a_{32}^2 \sigma_{22} + a_{33}^2 \sigma_{33})$$

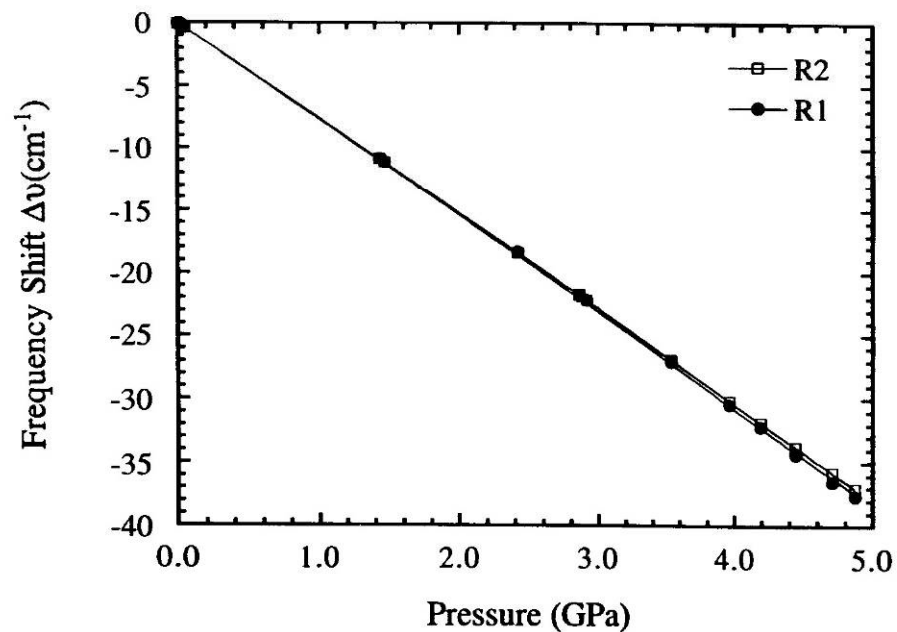
$$+ 2(\pi_{33} - \pi_{11})(a_{31} a_{32} \sigma_{12} + a_{31} a_{33} \sigma_{13} + a_{32} a_{33} \sigma_{23})$$
- Pure Hydrostatic stress

$$\Delta v = (2\pi_{11} + \pi_{33}) P$$

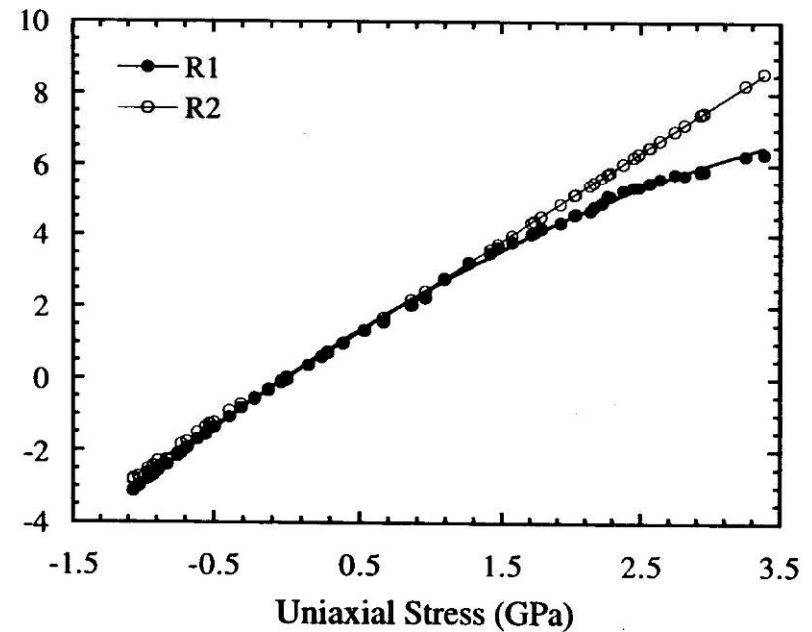
Calibration for polycrystalline, randomly oriented alumina

$$\sigma_{ij}^* = a_{ik} a_{jl} \sigma_{kl} \quad \overline{\Delta\nu} = \iiint P(\theta, \phi, \psi) \Delta\nu d\theta d\phi d\psi$$

$$\overline{\Delta\nu} = \frac{1}{3}(\Pi_{11} + \Pi_{22} + \Pi_{33})(\sigma_{11} + \sigma_{22} + \sigma_{33})$$

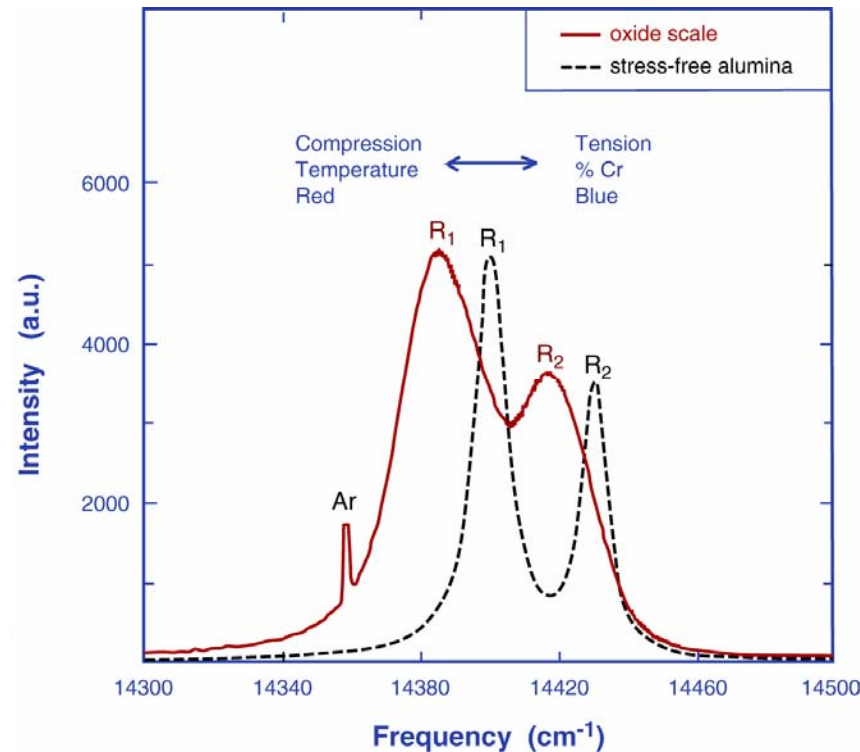


Hydrostatic stress



Uniaxial Compression to tension

Summary of Luminescence Shifts



Piez spectroscopic Shift:

$$\Delta\nu = \Pi_{ij} \sigma_j^* + \Lambda_{ijkl} \sigma_j^* \sigma_k^*$$

(For polycrystalline alumina: $\Delta\nu = (\Pi_{11} + \Pi_{22} + \Pi_{33}) (\sigma_{11} + \sigma_{22} + \sigma_{33})$)

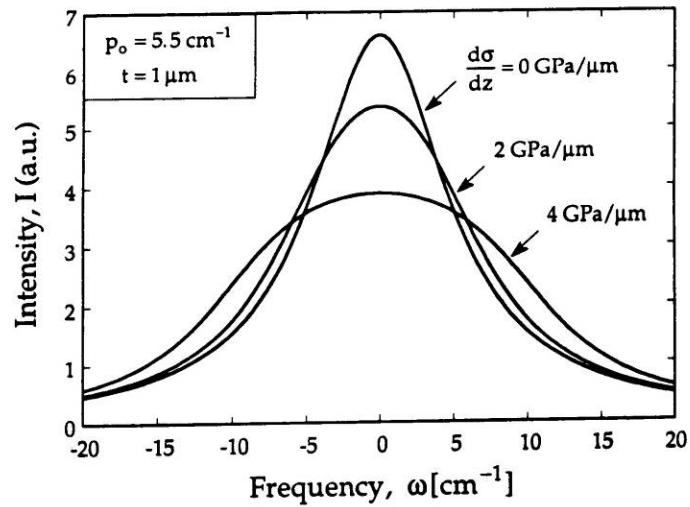
Temperature Shifts:

$$\nu(T) = \nu(T_o) + \alpha(T - T_o) \quad \alpha_{R1} = -0.144 \quad \alpha_{R2} = -0.134 \quad \text{cm}^{-1}/\text{C}$$

Concentration Shift:

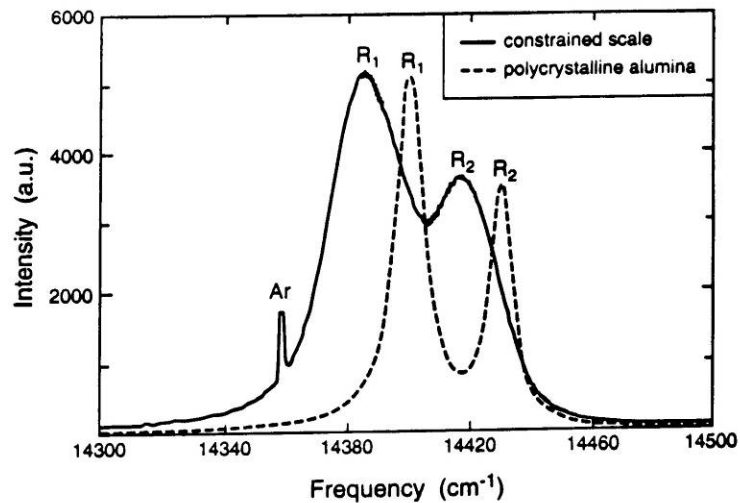
$$\nu(\%Cr) = \nu_o + 0.99 a/o Cr \quad \text{cm}^{-1}$$

Effect of Stress Gradient

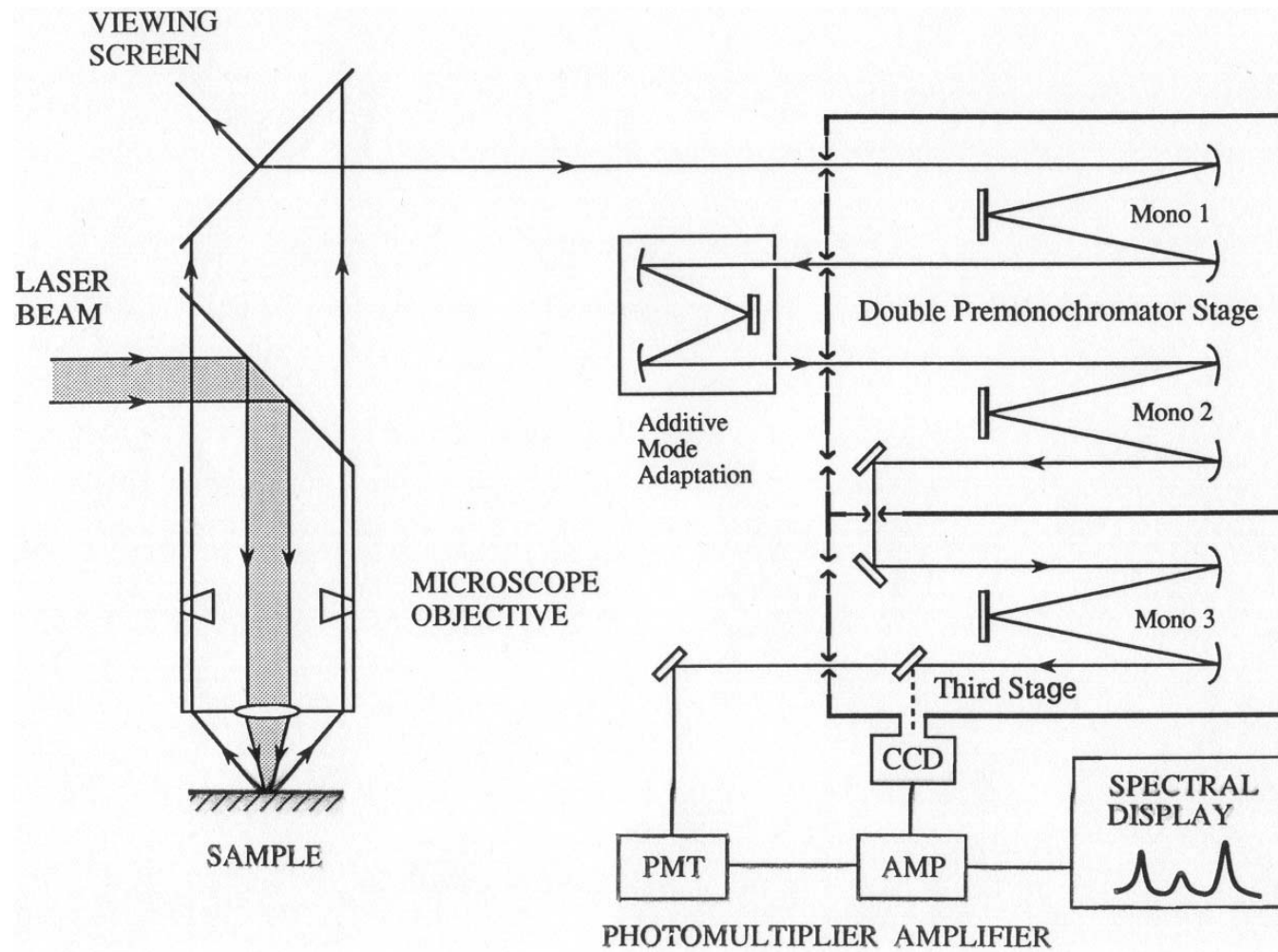


Stress gradient causes peak broadening

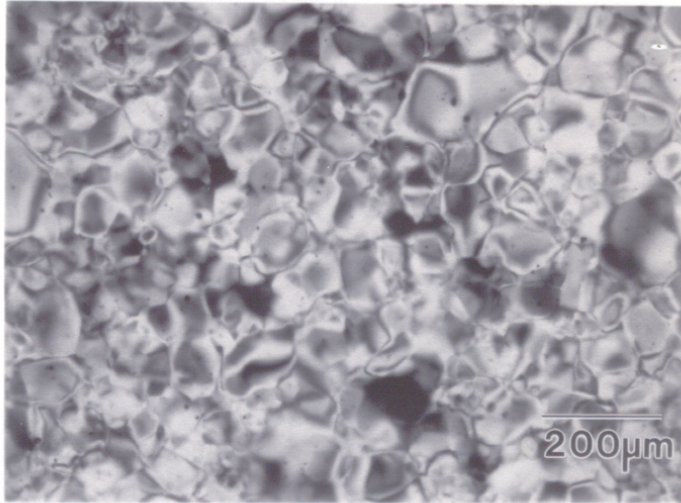
$$\frac{d\sigma}{dz} = \frac{3}{t \Pi_{ii}} \sqrt{(w^2 - w_o^2)}$$



Optical Microprobe Configuration

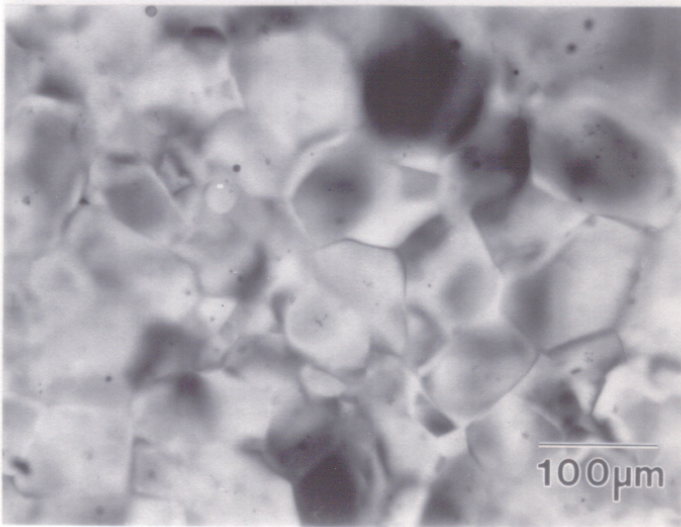


Internal Stress Distribution in Polycrystalline Alumina



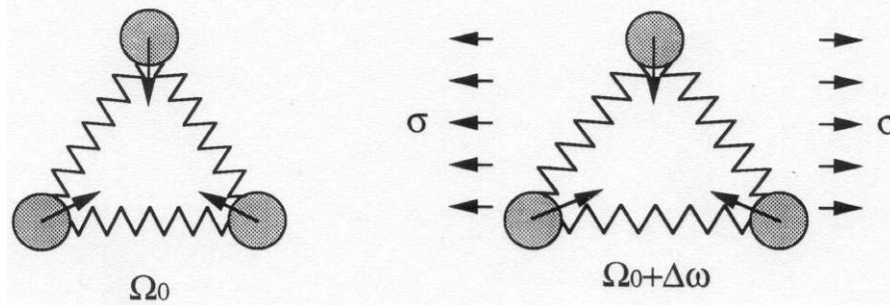
Observation in transmitted light through cross-polarizers of alumina.

Variation in stress made visible through the piezo-optical effect.

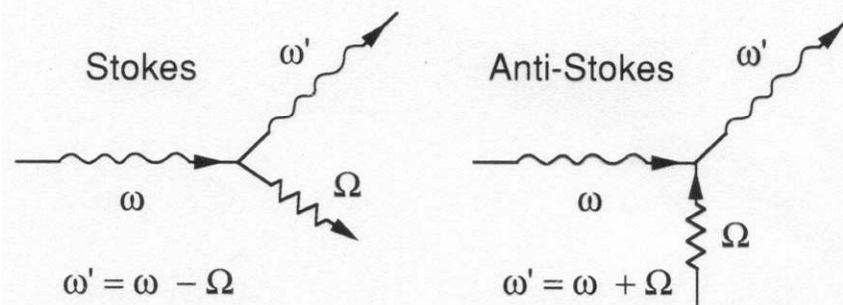


Raman Piezospectroscopy

Raman Piezospectroscopy



Normal Vibration Modes

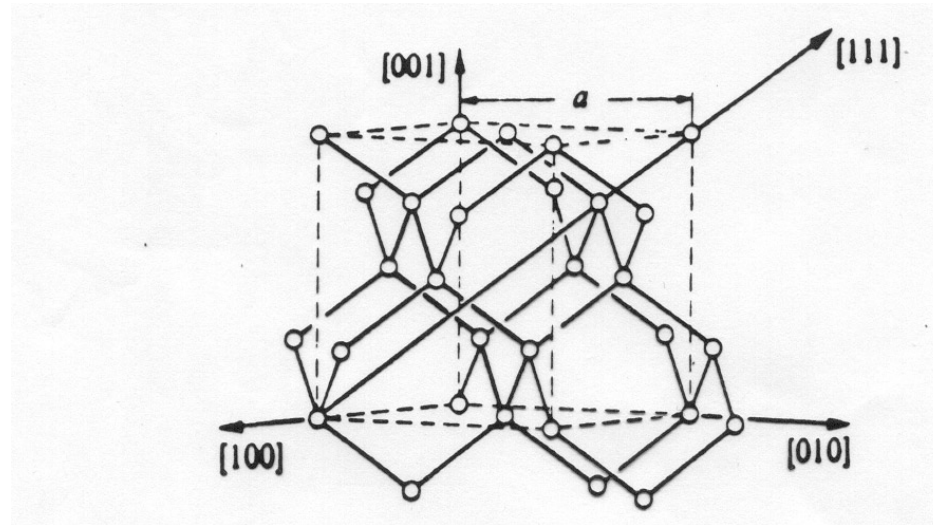


Raman Process

Intensity Ratio

$$\frac{I_{AS}}{I_S} = \left(\frac{\omega + \Omega}{\omega - \Omega} \right)^3 \frac{(\Sigma / \alpha)_{AS}}{(\Sigma / \alpha)_S} \exp \left(-\frac{\hbar \Omega}{k_B T} \right)$$

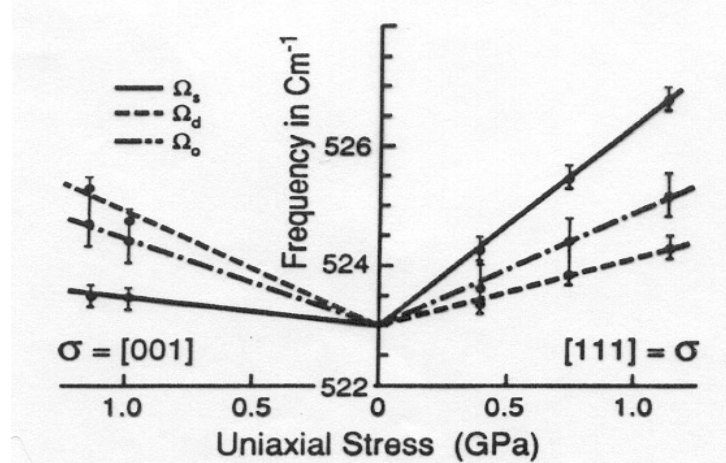
Raman Piezospectroscopy of Silicon



Active vibrational modes

Transverse Optical --- TO1 along [100], TO2 along [010]

Longitudinal Optical – LO along [001]



Raman Piezospectroscopy

1. Strain-free c-Si Polarizability tensor

$$\mathbf{R}_1 = \overset{\text{TO}_1}{\begin{pmatrix} 0 & 0 & 0 \\ 0 & 0 & 1 \\ 0 & 1 & 0 \end{pmatrix}} \quad \mathbf{R}_2 = \overset{\text{TO}_2}{\begin{pmatrix} 0 & 0 & 1 \\ 0 & 0 & 0 \\ 1 & 0 & 0 \end{pmatrix}} \quad \mathbf{R}_3 = \overset{\text{LO}}{\begin{pmatrix} 0 & 1 & 0 \\ 1 & 0 & 0 \\ 0 & 0 & 0 \end{pmatrix}}$$

Scattering efficiency

$$S = A \sum_j |\mathbf{e}_j \cdot \mathbf{R}_j \cdot \mathbf{e}_s|^2$$

Raman line frequency $\nu_0 = 520 \text{ Rcm}^{-1}$

2. In the presence of a strain ϵ_{ij}

$$\begin{vmatrix} p\epsilon_{XX} + q(\epsilon_{YY} + \epsilon_{ZZ}) - \lambda & 2r\epsilon_{XY} & 2r\epsilon_{XZ} \\ 2r\epsilon_{XY} & p\epsilon_{YY} + q(\epsilon_{XX} + \epsilon_{ZZ}) - \lambda & 2r\epsilon_{YZ} \\ 2r\epsilon_{XZ} & 2r\epsilon_{YZ} & p\epsilon_{ZZ} + q(\epsilon_{XX} + \epsilon_{YY}) - \lambda \end{vmatrix} = 0$$

Eigenvalues $\lambda_{ij} = \nu_i^2 - \nu_0^2$, $i = 1, 2, 3$

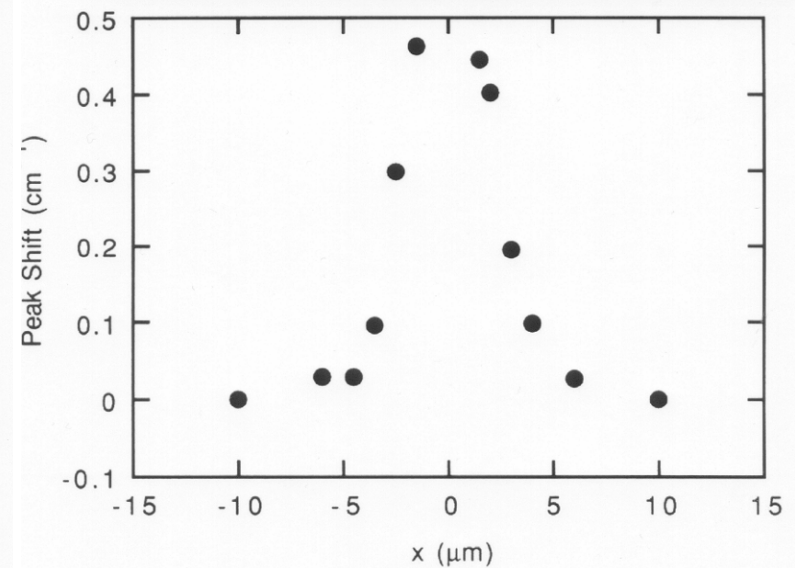
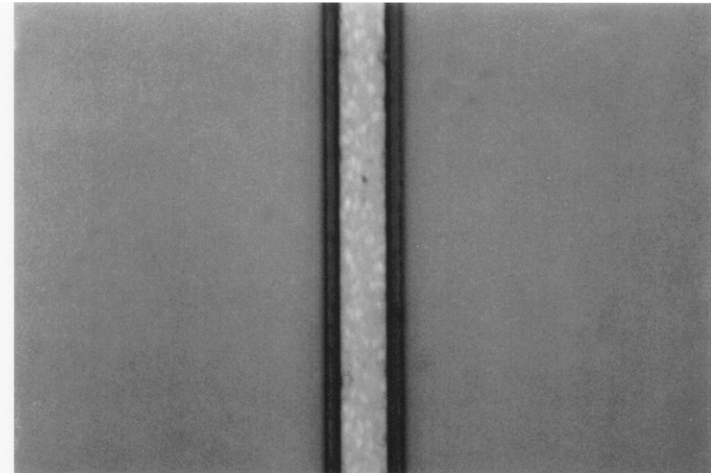
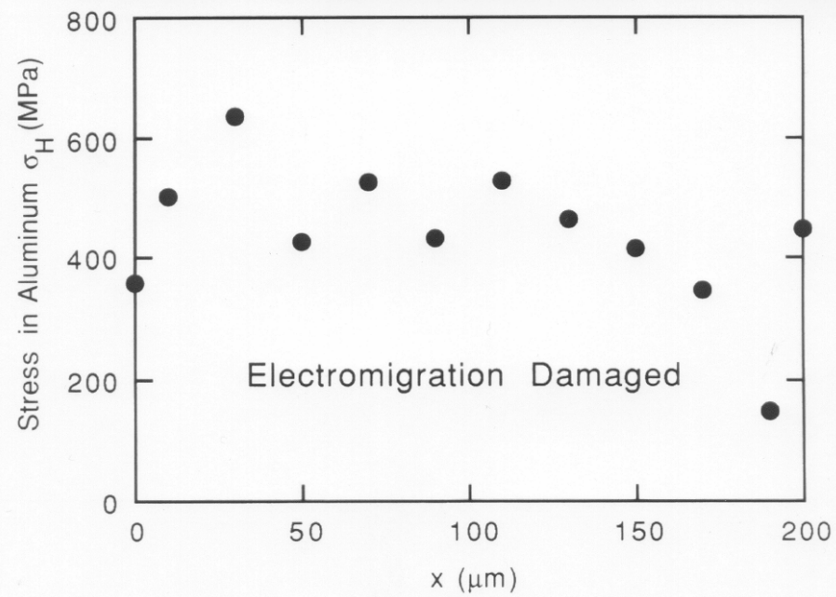
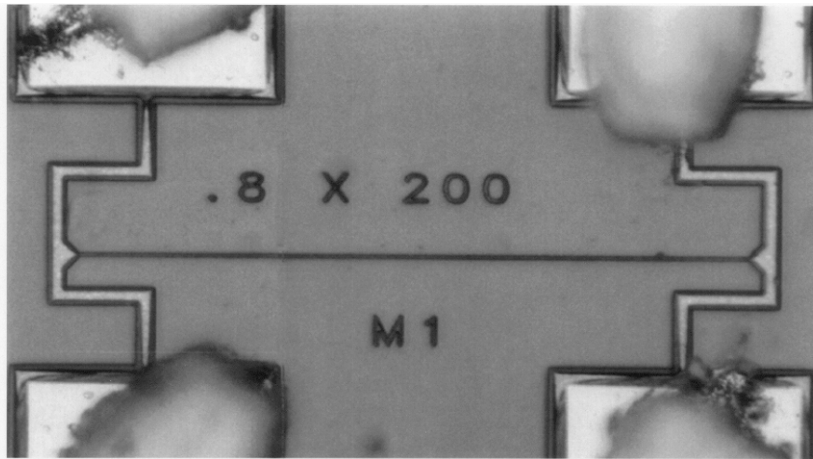
Frequency shift

$$\Delta\nu_i = \nu_i - \nu_0 \cong \lambda_i / 2\nu_0$$

Deformation Potentials (Anastassakis, 1985)

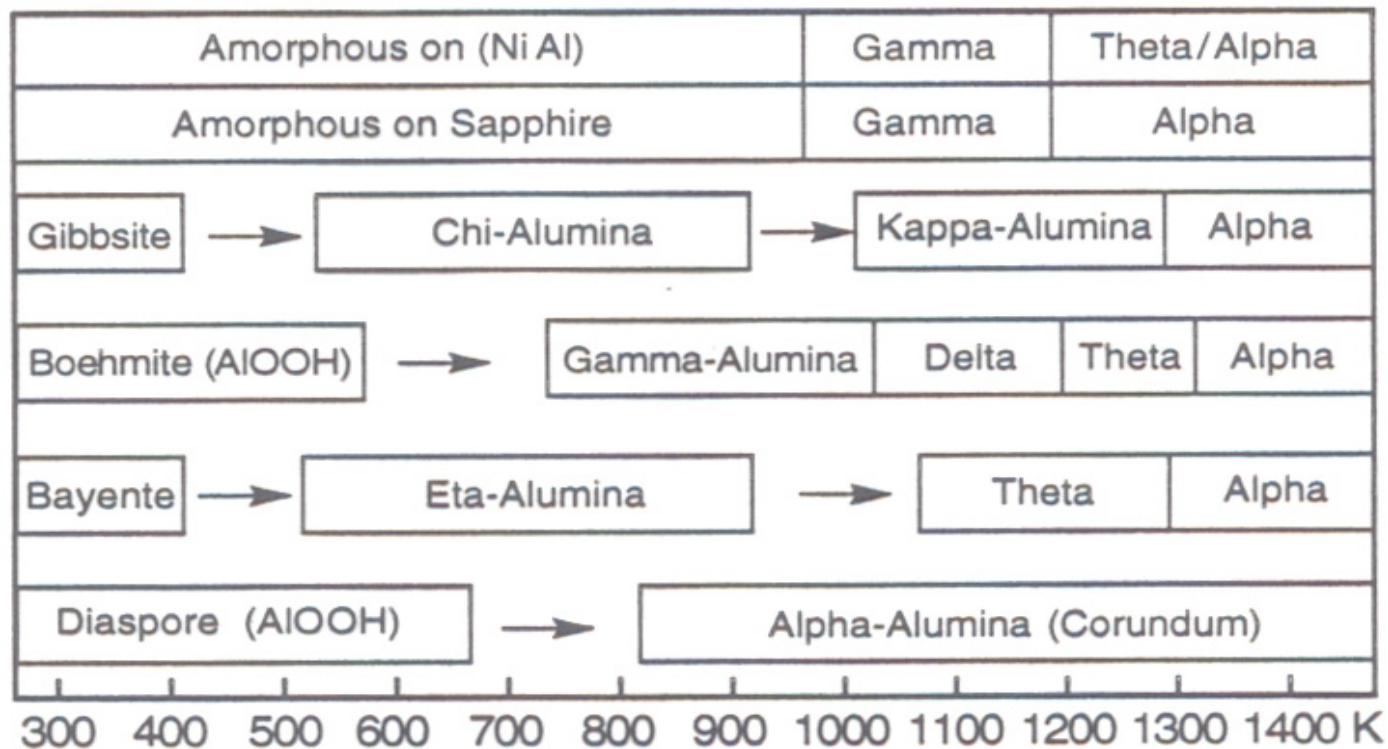
$$p = -1.43\nu_0^2, \quad q = -1.89\nu_0^2, \quad r = -0.59\nu_0^2$$

Raman Piezospectroscopy In Electromigration

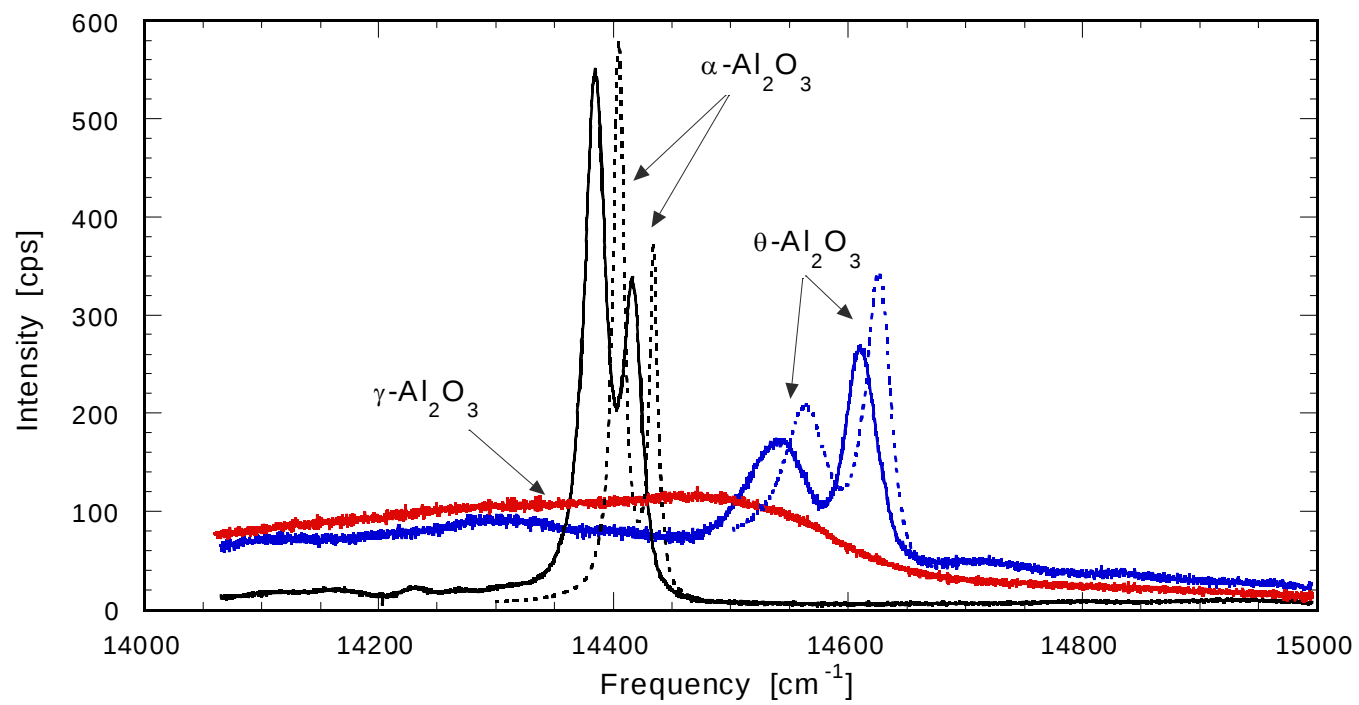


Phase Transformations in Alumina During High Temperature Oxidation

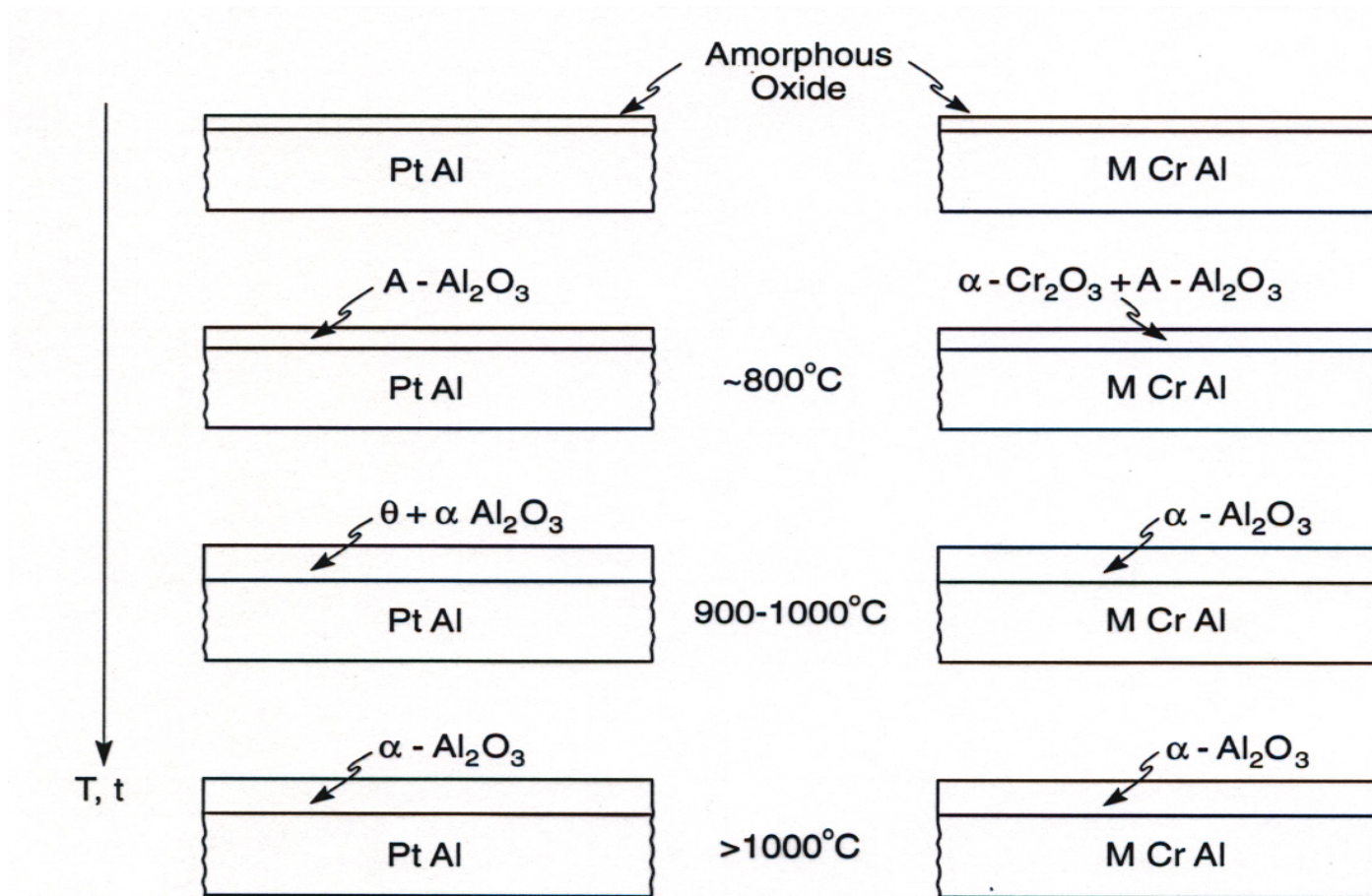
Reported Phase Transformations in Alumina Ceramics, Powders and Films



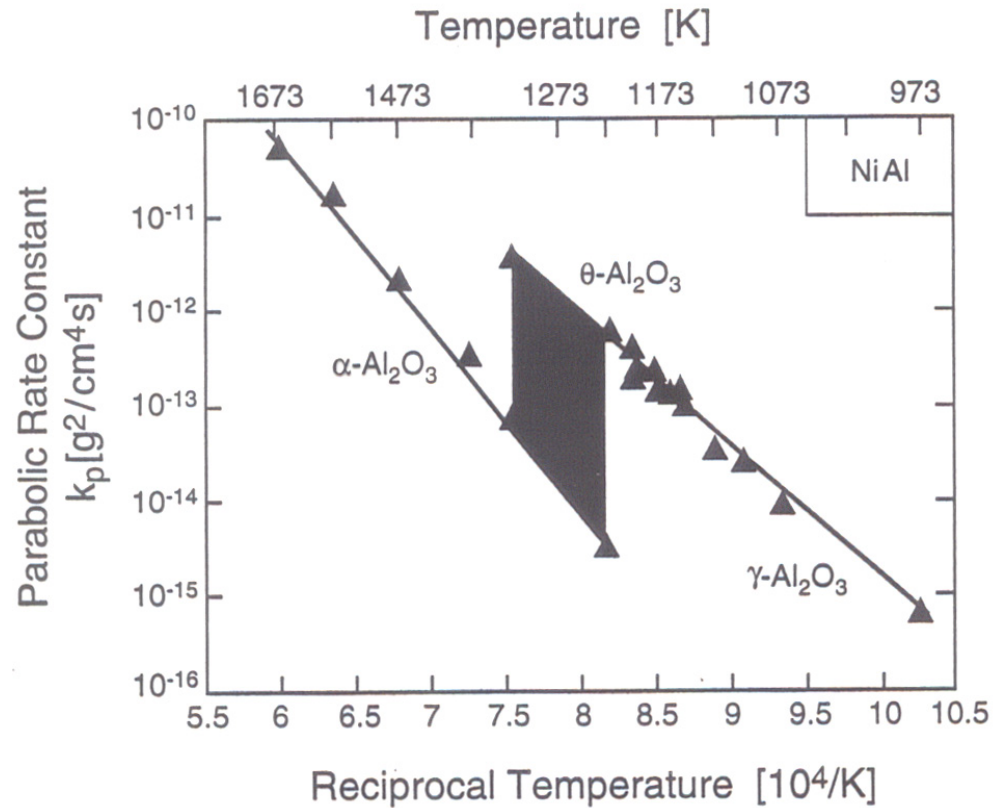
Luminescence Identification of Alumina Phases



Oxidation Induced Transformation Sequence on MCrAl vs NiPtAl



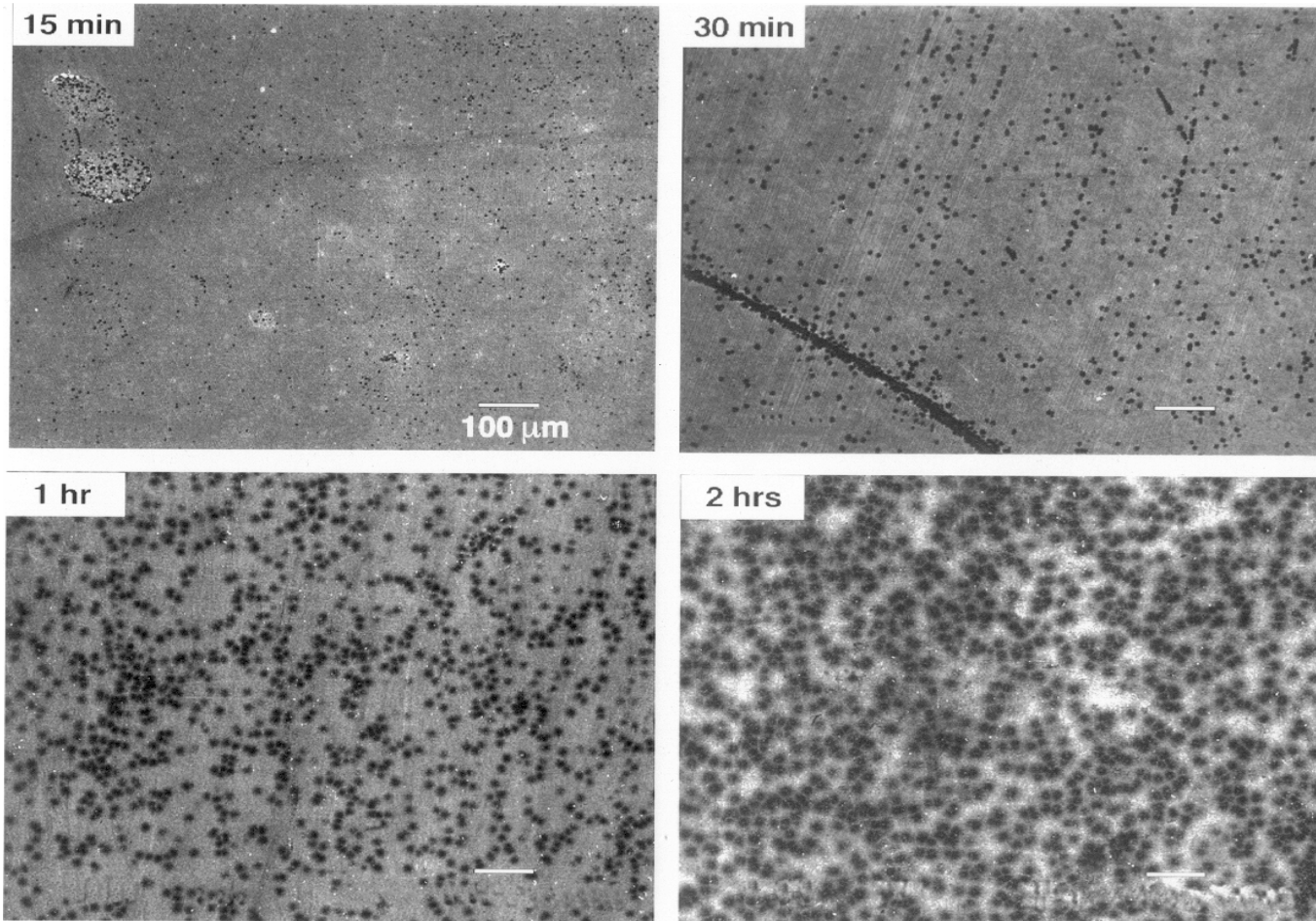
Alumina Transformation Kinetics on NiAl



Phase identification by X-ray diffraction

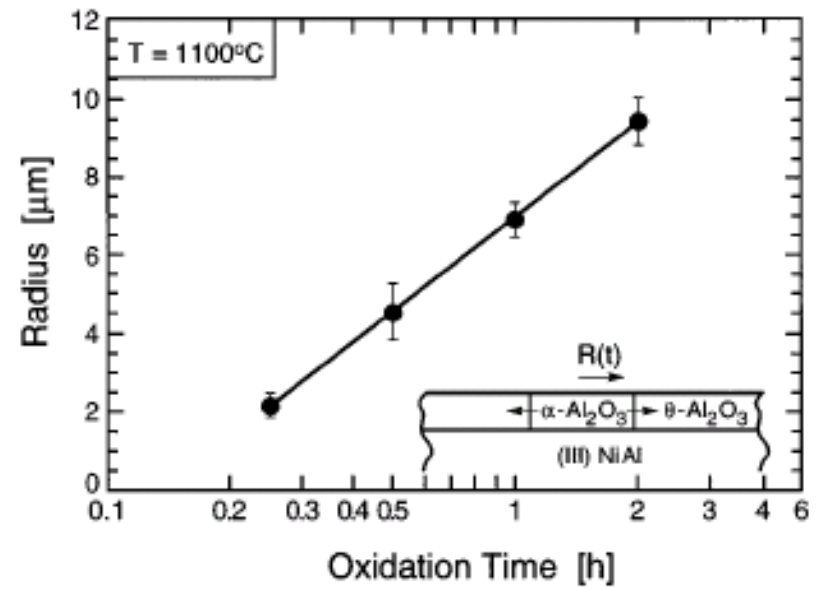
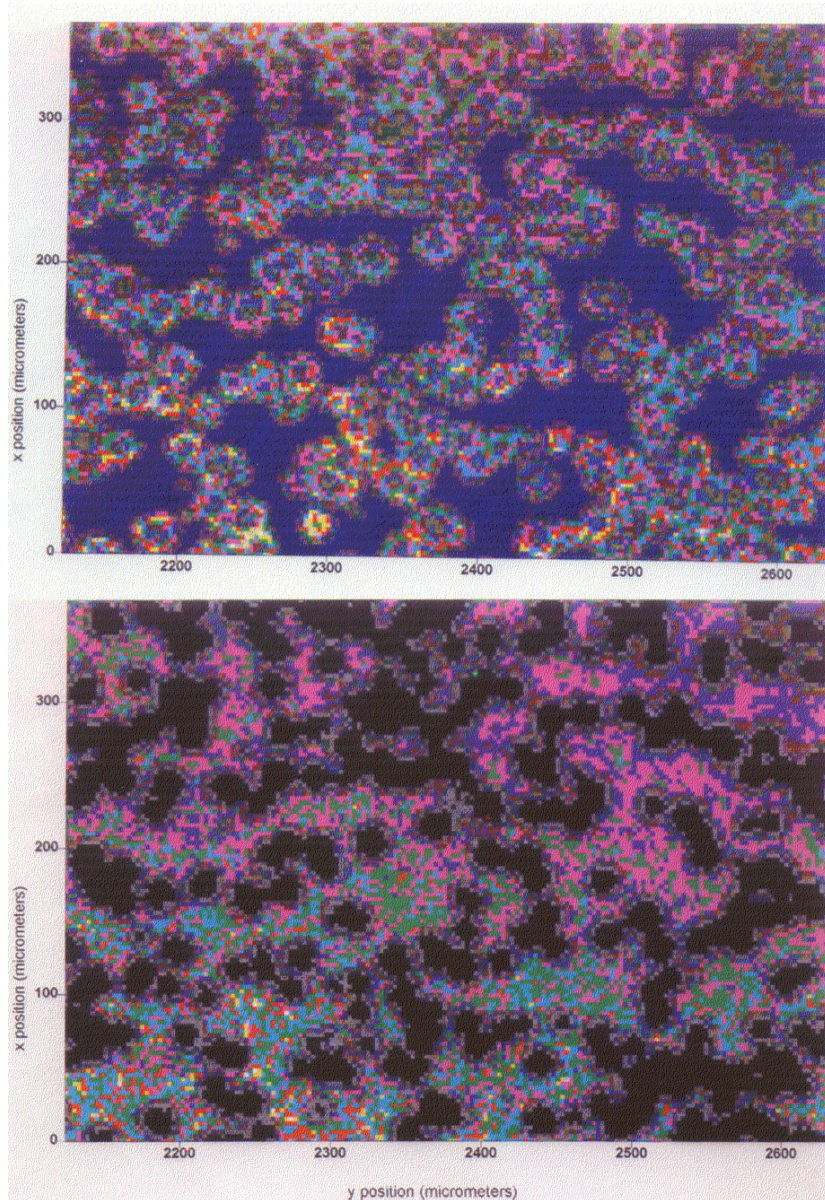
Grumm and Grabke

Nucleation and Growth of α -alumina on NiAl



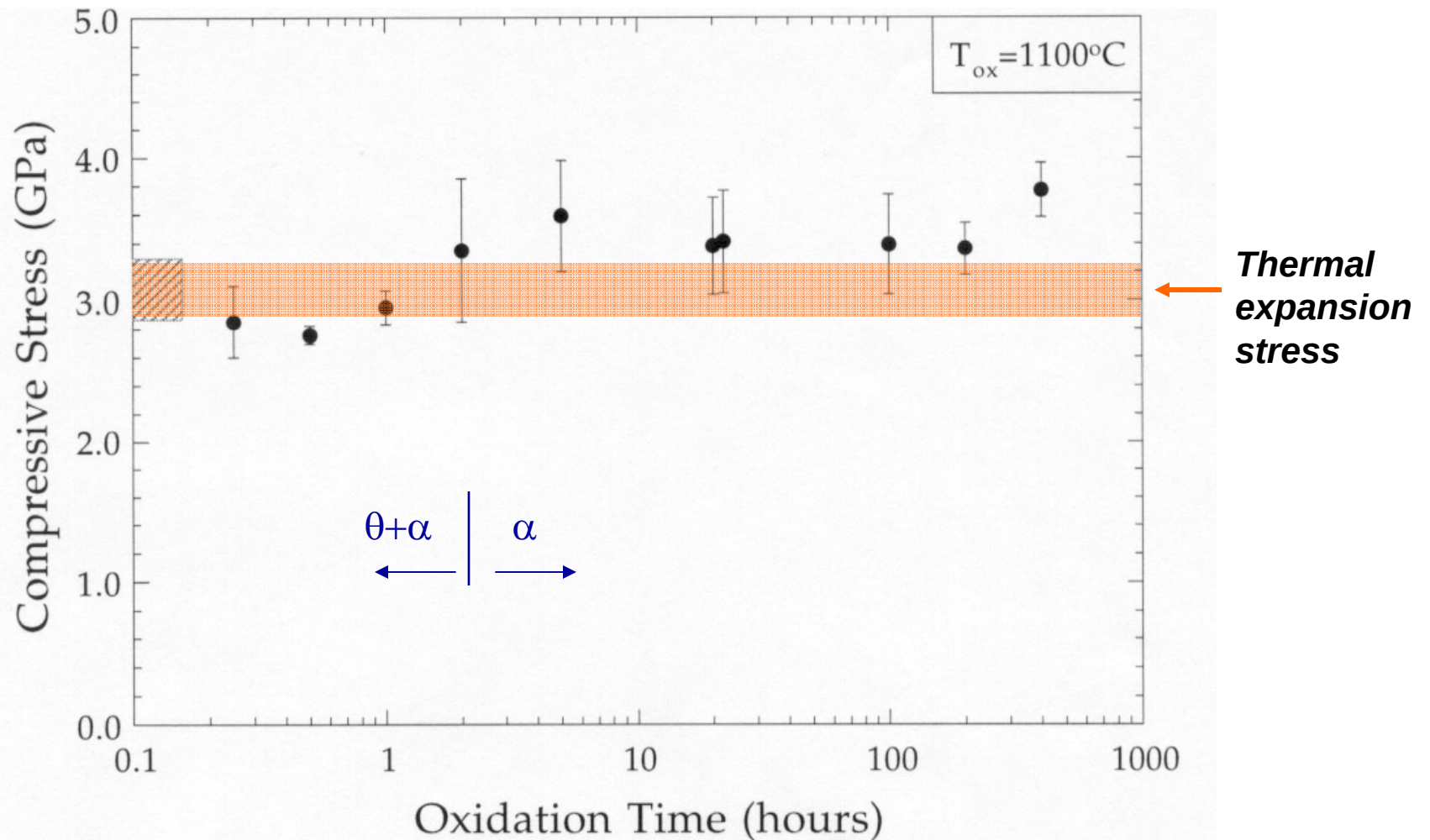
Oxidation Temperature 1100°C

Luminescence Mapping For Transformation Kinetics



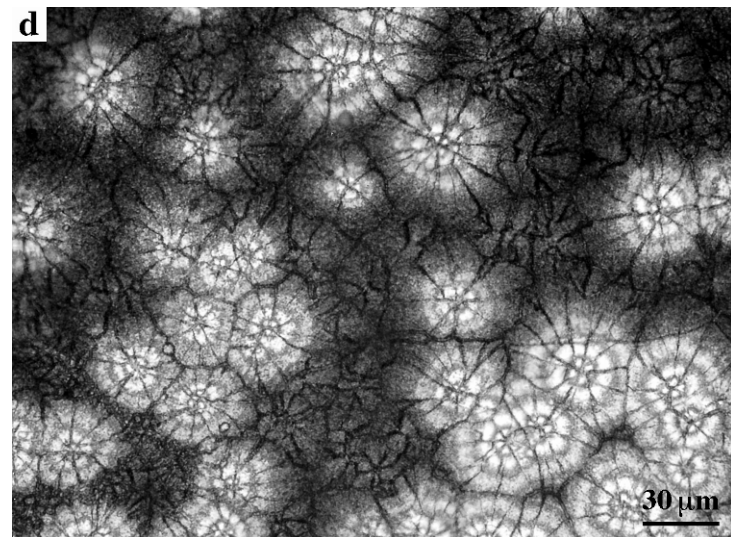
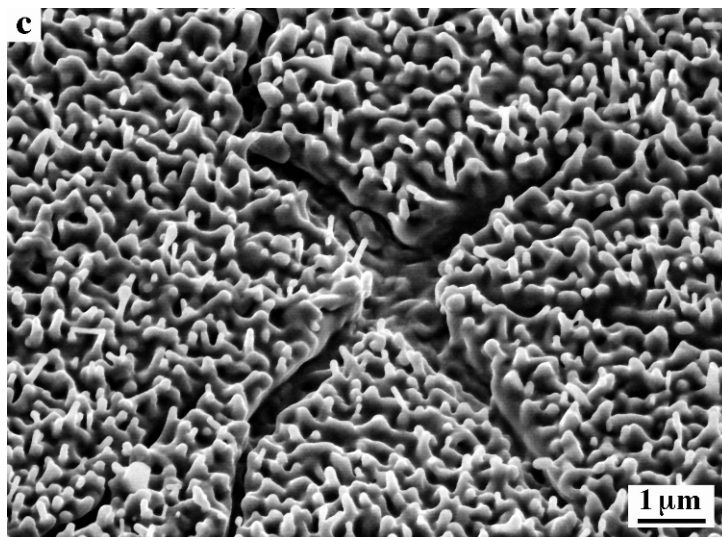
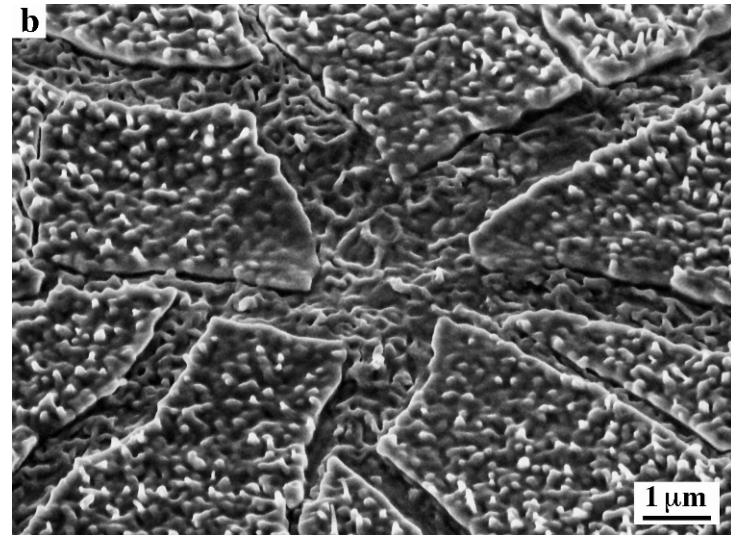
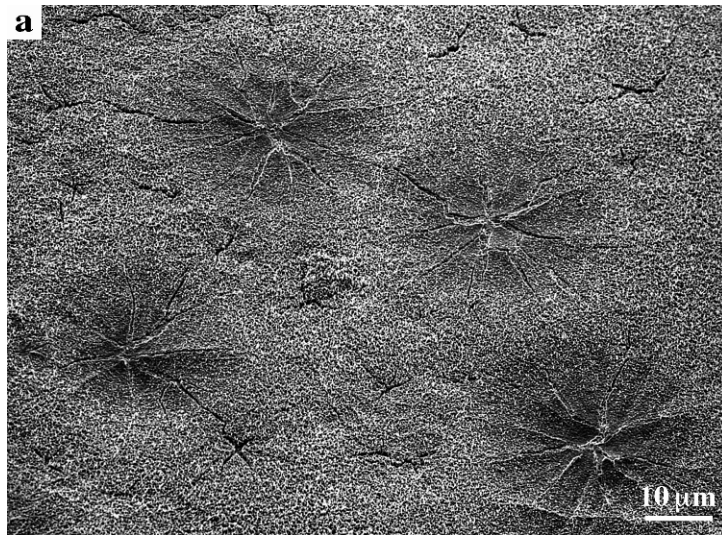
$$R = A + B \log t$$

Evolution of Stress in NiAl Single Crystal

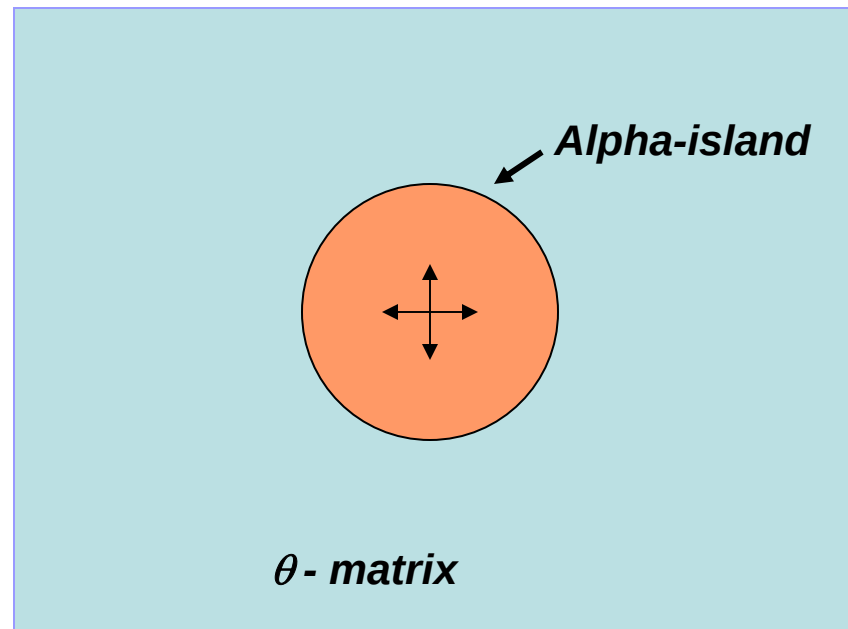


NB. Alpha phase is under net tension under transformation is complete. Then oxide is under compression.

Nucleation and Growth of α -Alumina During Oxidation



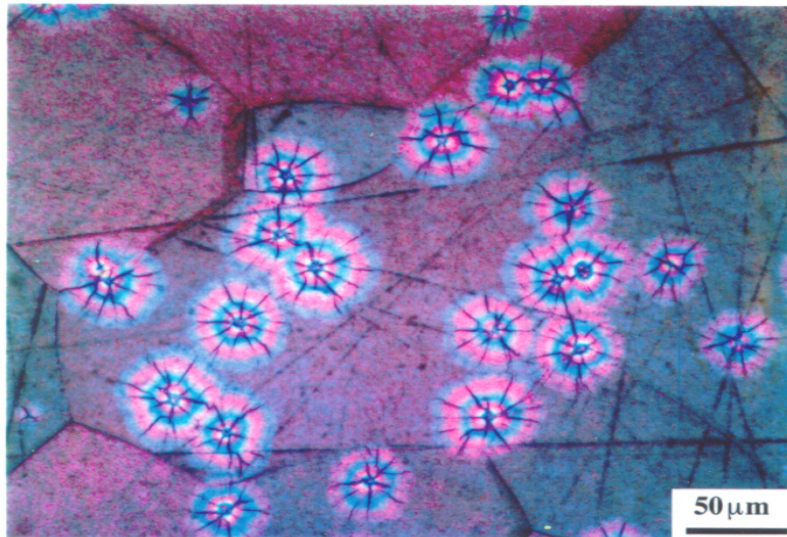
Origin of Transformation Stresses



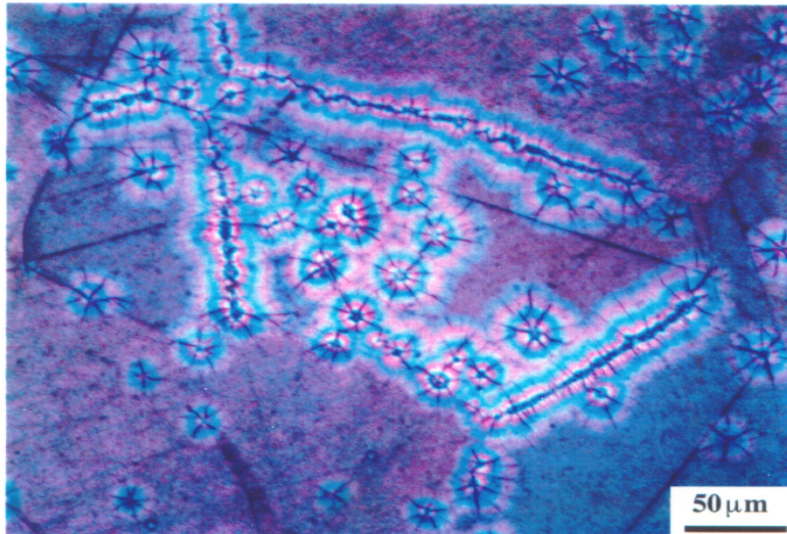
$\theta \rightarrow \alpha$ transformation is accompanied by a 9.5 % volume decrease.

The transformation is constrained by the surrounding θ oxide, placing the α - islands under tension. This causes “tearing” of islands.

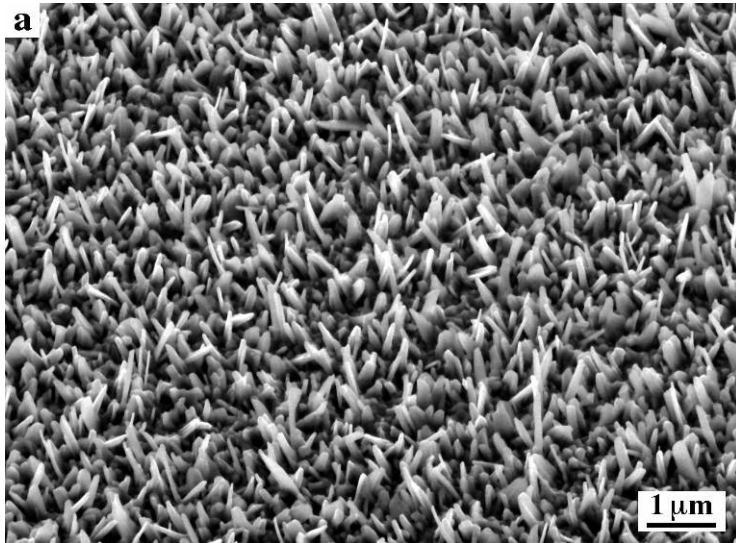
Heterogeneous Nucleation and Growth of α -alumina on NiAl



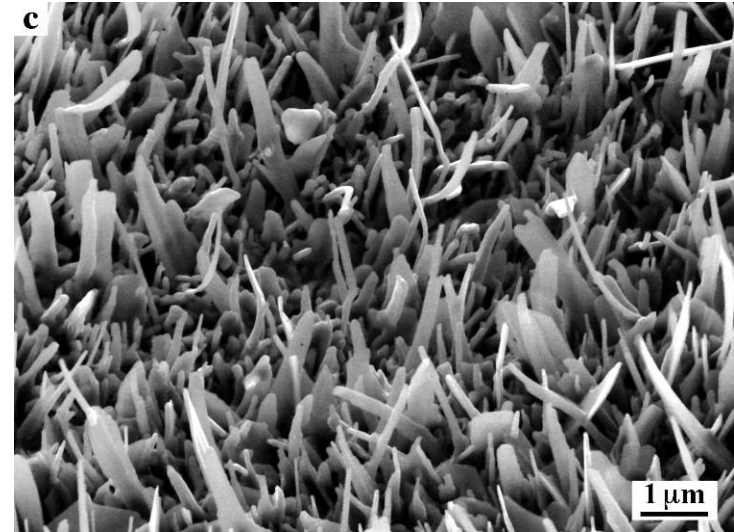
Note the radial cracks in the islands, giving the “star” contrast



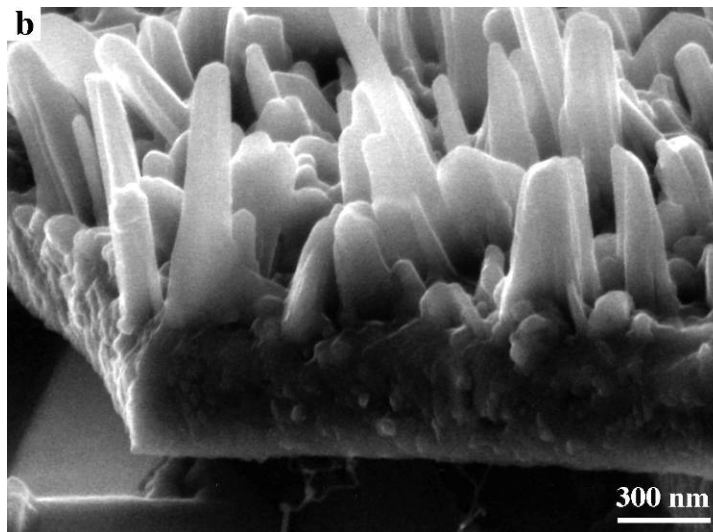
TGO Morphology at 1000°C



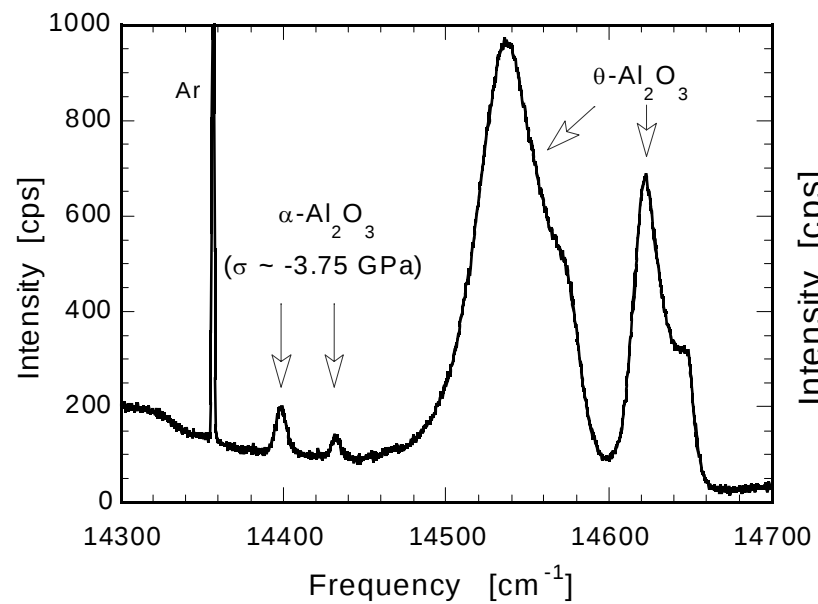
1 hour $\theta \sim 0.5 \mu\text{m}$ thick



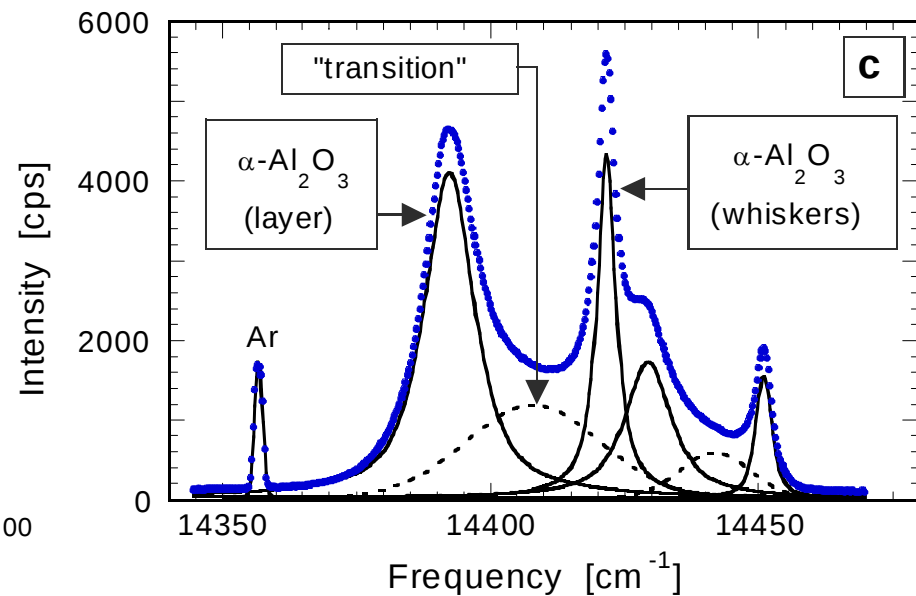
25 hour mixed $\alpha + \theta$



Fibrous θ -phase Transforms to α -alumina



1 hour at 1100°C

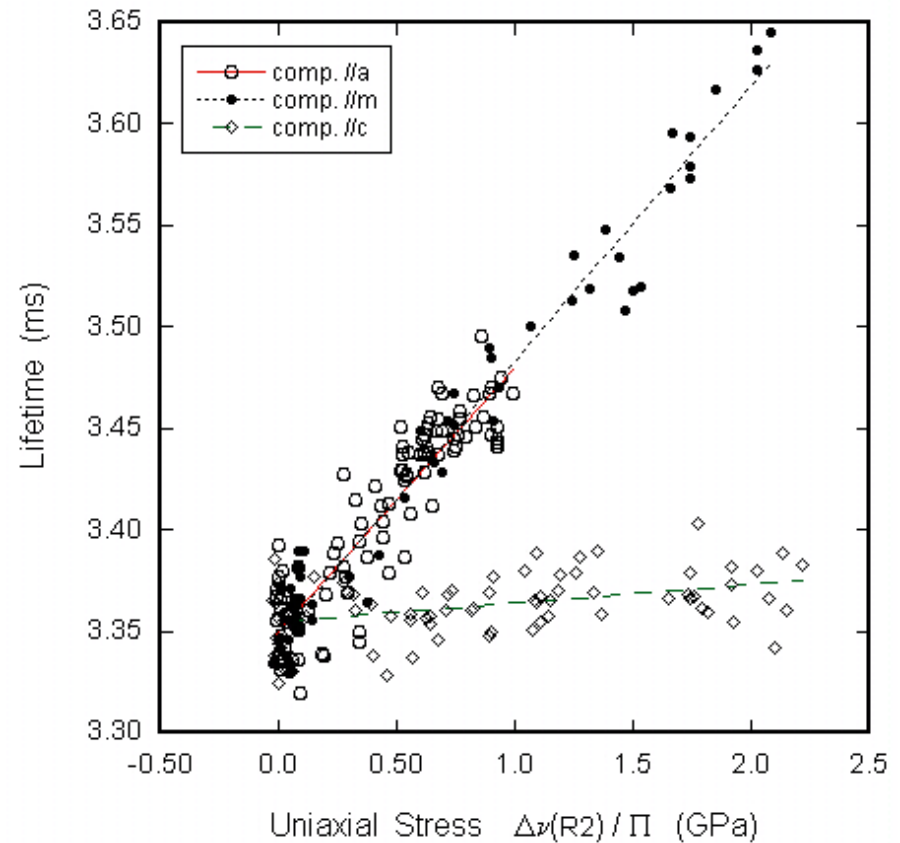
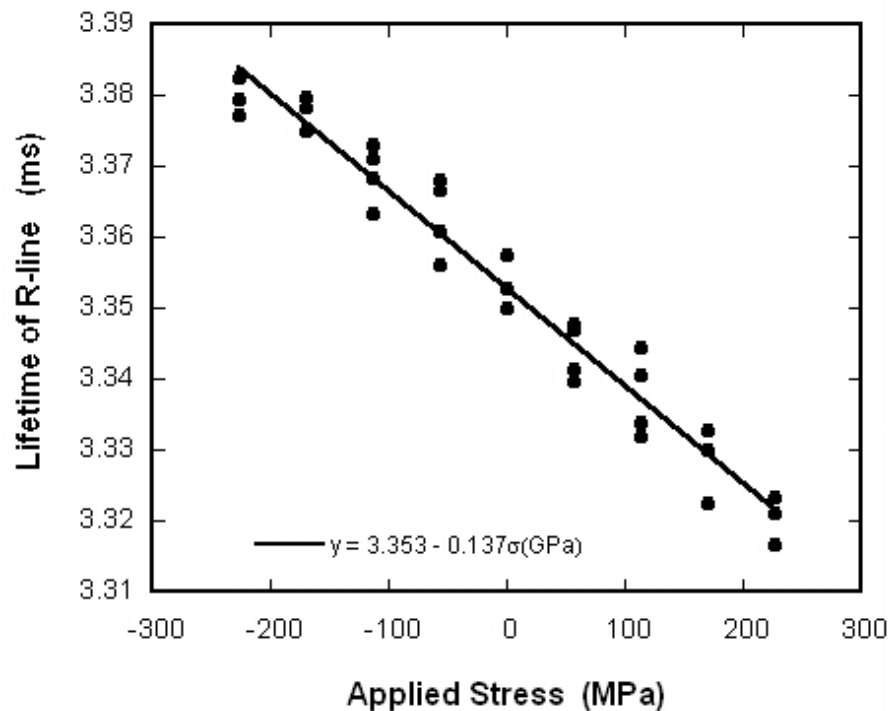


25 hour at 1100°C

Recent Developments

Stress Effects on the Luminescence Lifetime

Polycrystalline alumina

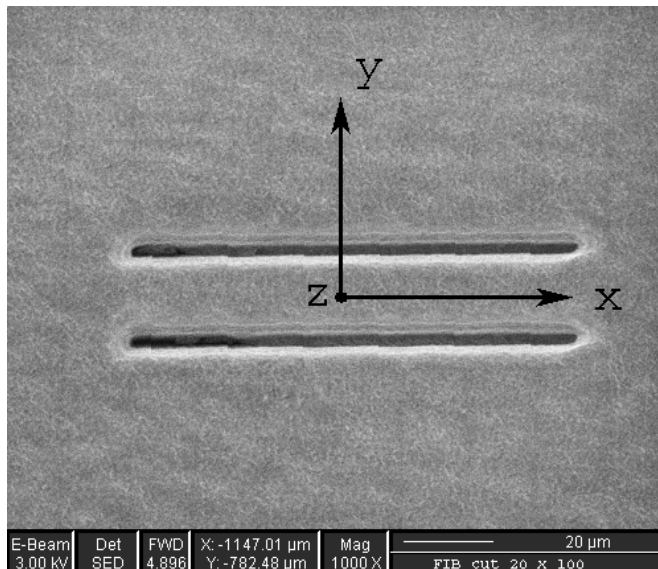


Lifetime varies with crystallographic direction and linearly with stress

Use of Polarization to Distinguish Stress Components

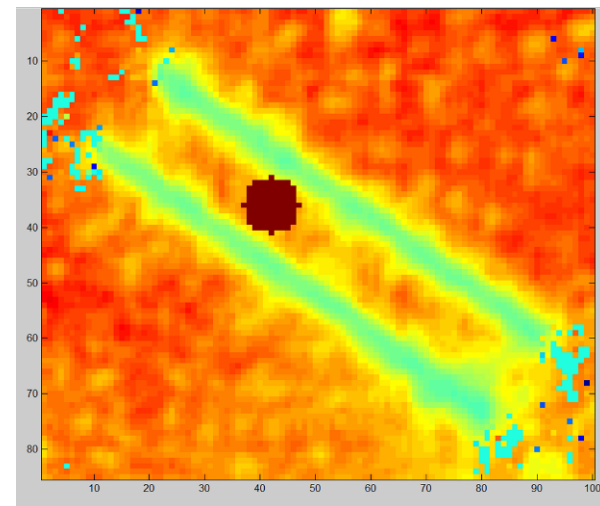
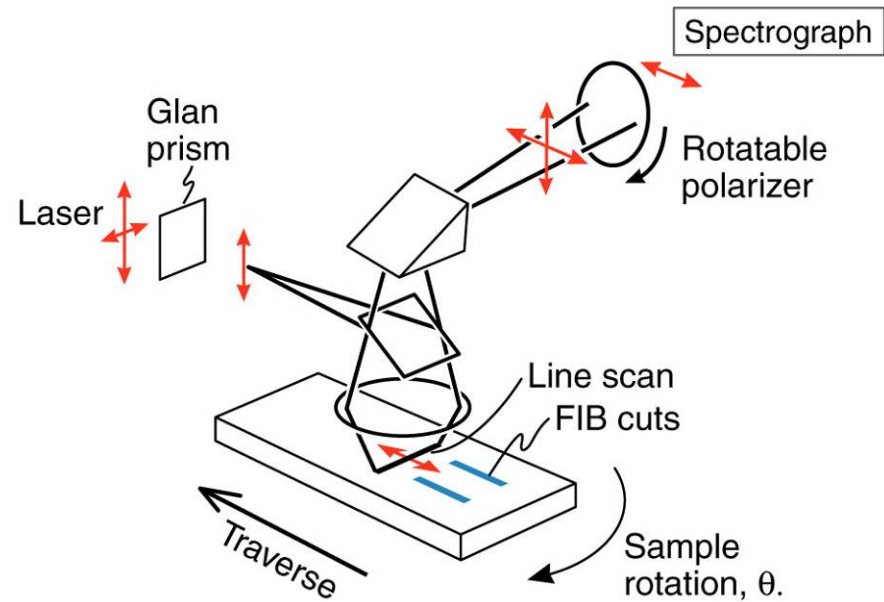
Frequency shift proportional to mean stress in polycrystalline alumina:

$$\Delta \nu_{R2} = 7.62 (\sigma_{xx} + \sigma_{yy} + \sigma_{zz}) / 3$$



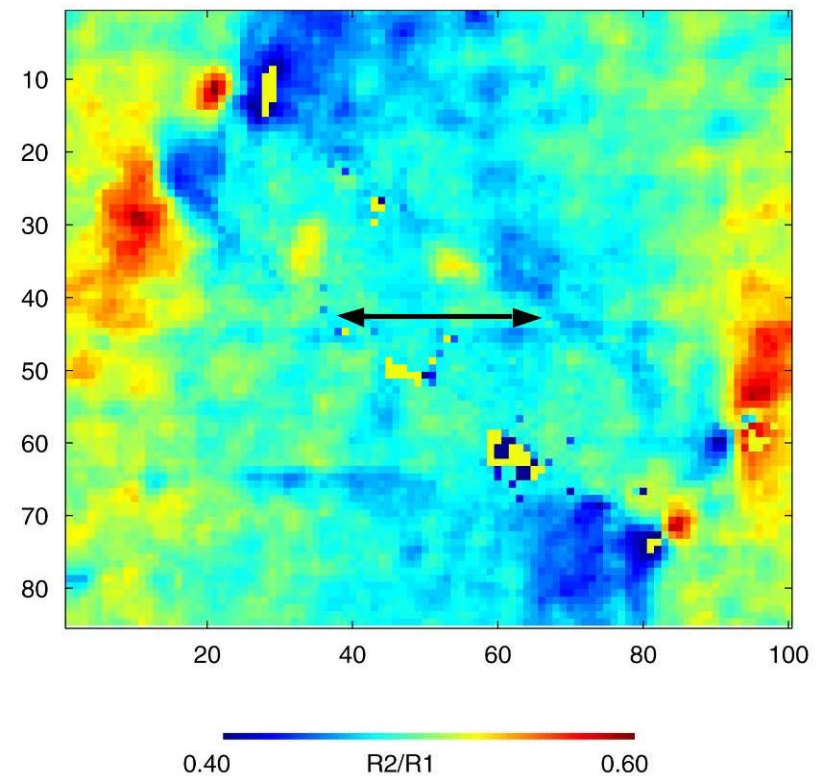
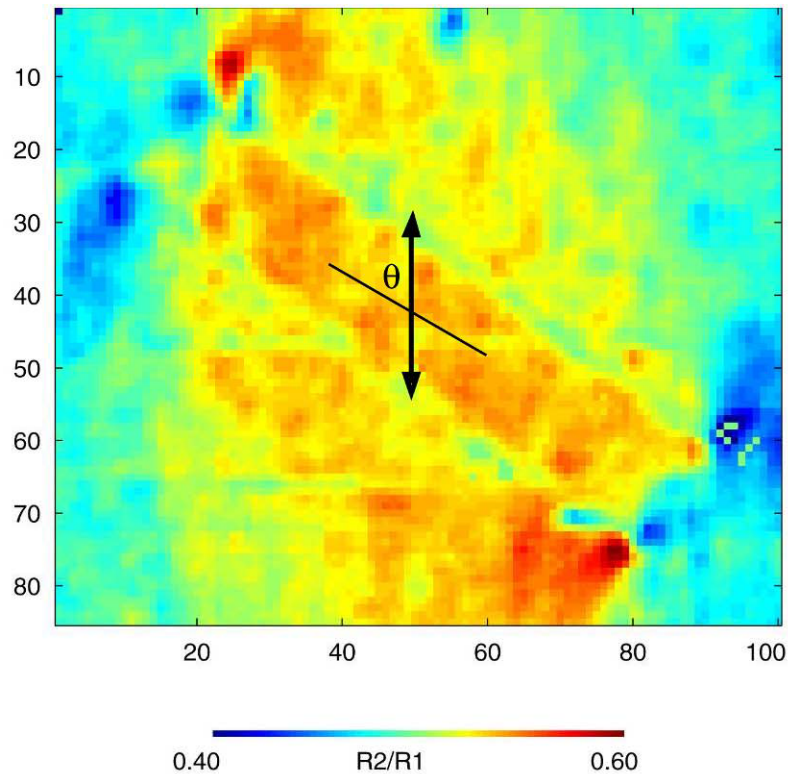
FIB cuts create a strip under uniaxial stress

Luminescence intensity map around strip



Use of Polarization to Distinguish Stress Components

Imaging under different polarization conditions reveals directions of principal stresses by affecting R2/R1 peak area ratio.



End of Part I